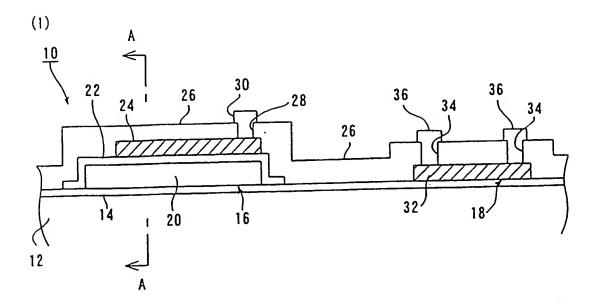
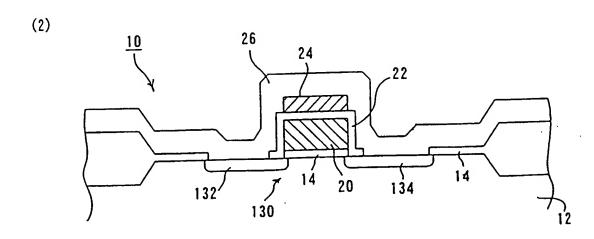
## FIG. 1





10: Semiconductor device

12: Semiconductor substrate

14: Insulating layer

16: Capacitive element section

18: Resistance element section

20: Gate electrode

22: Dielectric layer

24: Capacity electrode

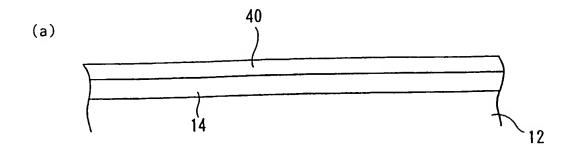
26: Insulating film

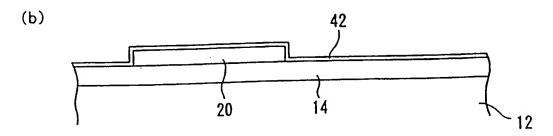
30: Drawer electrode

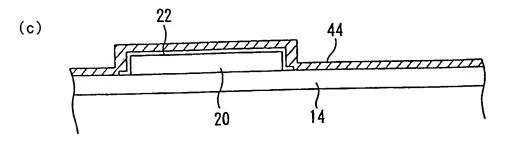
32: Resistance element body

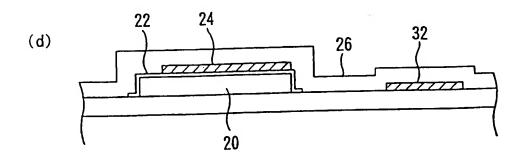
130: MOS transistor

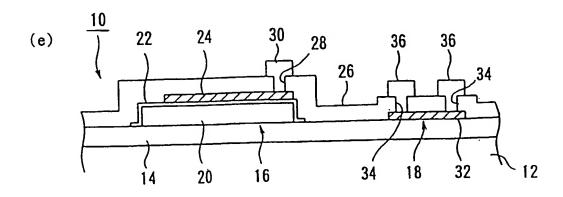
## FIG. 2

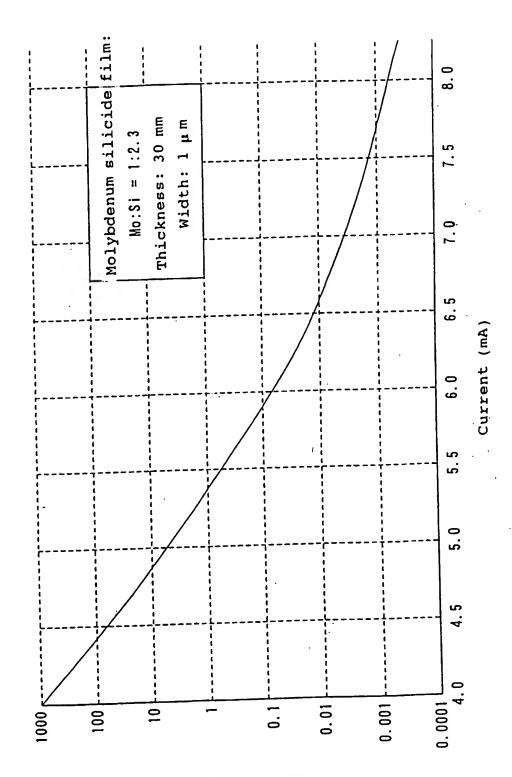






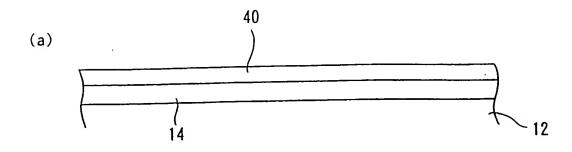


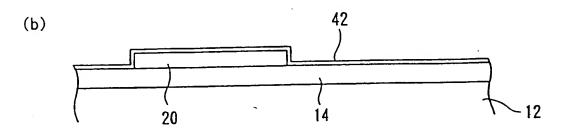


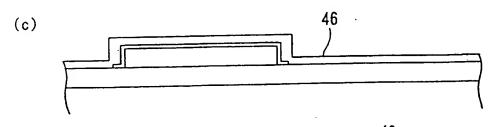


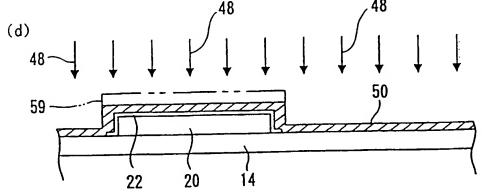
Blowout time (sec)

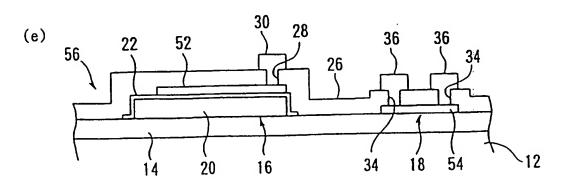
FIG. 4

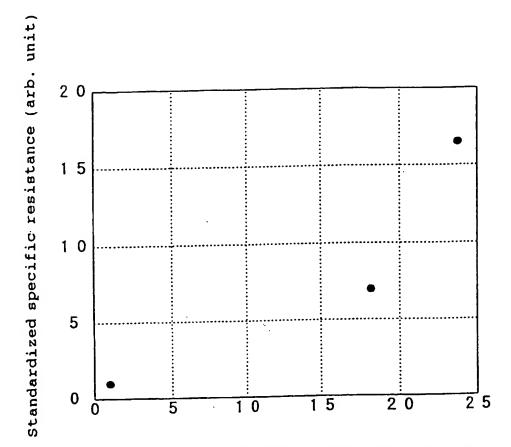






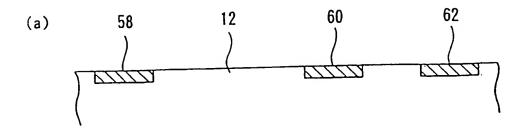


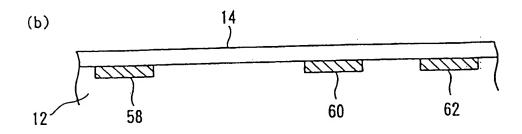


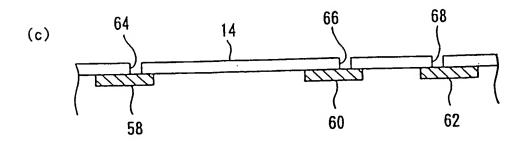


Oxygen atomic weight in TiN film (at. %)

FIG. 6







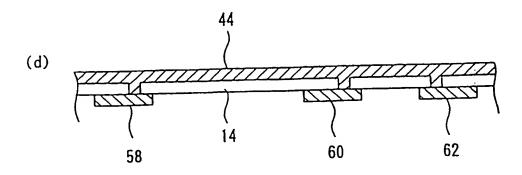
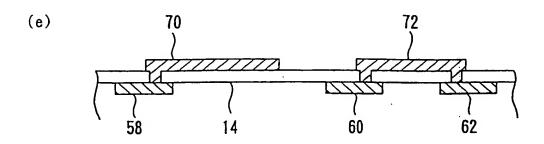
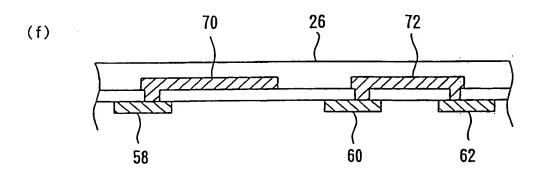
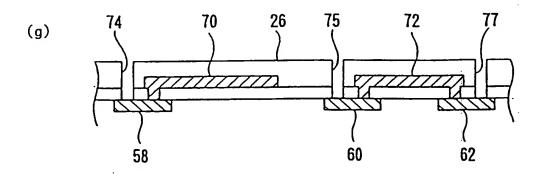


FIG. 7







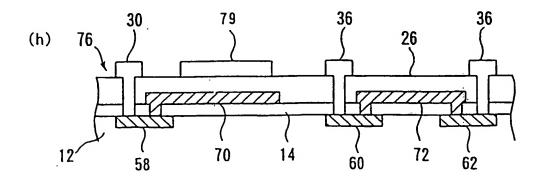
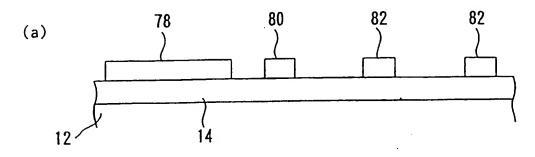
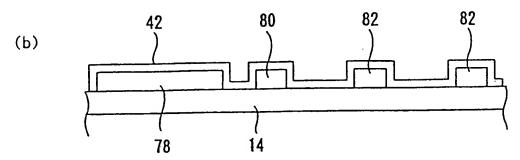
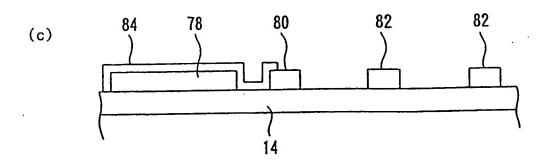
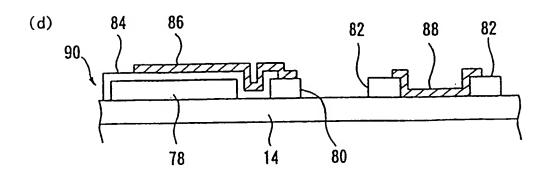


FIG. 8

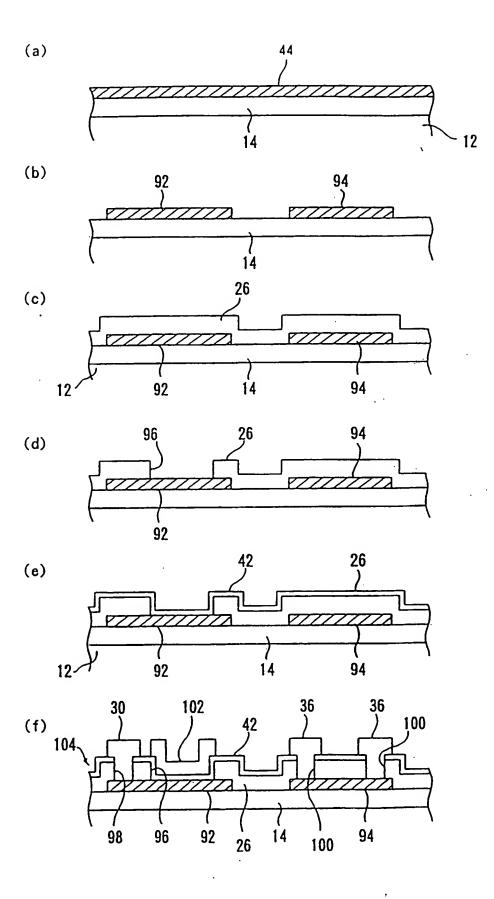








F1G.9



F1G. 10

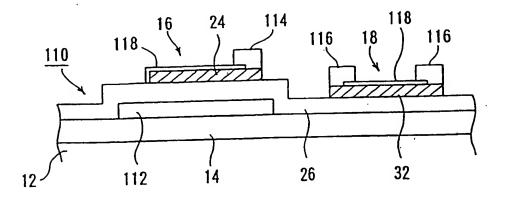


FIG. 11

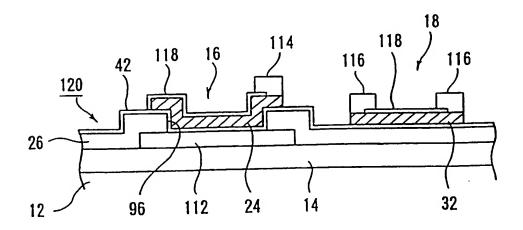


FIG. 12

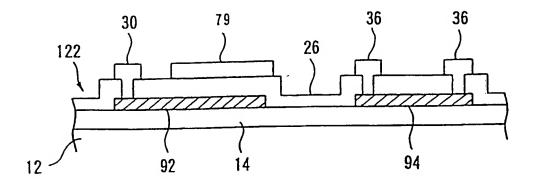


FIG. 13

